

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of: Bruno GHYSELEN et al.

Confirmation No.

Application No.:

Group Art Unit:

Filing Date: February 20, 2004

Examiner:

For: METHOD FOR FORMING A RELAXED OR
PSEUDO-RELAXED USEFUL LAYER ON A
SUBSTRATE

Atty. Docket No.: 4717-10200

INFORMATION DISCLOSURE STATEMENT

Commissioner for Patents
P.O. Box 1450
Alexandria, Virginia 22313-1450

Sir:

Pursuant to applicants' duty of disclosure under 37 C.F.R. 1.56, enclosed are copies of sixteen (16) references for the Examiner's review and consideration. These references were cited in the specification of the application and in preliminary search report and a copy is enclosed.

These references are listed on the enclosed Form PTO-1449. It is respectfully requested that these references be made of record in this application by the Examiner's completion and return of the PTO Form 1449.

No fee or certification is believed to be due for this submission since the references are being submitted concurrent with the filing of this application. Should any fees be required, however, please charge such fees to **Winston & Strawn** Deposit Account No. 50-1814.

Respectfully submitted,

Date: _____

2/20/04



Allan A. Fanucci (Reg. No. 30,256)

WINSTON & STRAWN LLP
CUSTOMER NO. 28765
(212) 294-3311

Enclosures

LIST OF REFERENCES CITED BY APPLICANT <i>(Use several sheets if necessary)</i>					ATTY. DOCKET NO.:		APPLICATION NO.:	
					4717-10200			
					APPLICANT:			
					Bruno GHYSELEN et al.			
					FILING DATE:		GROUP:	
					February 20, 2004			
U.S. PATENT DOCUMENTS								
*EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE	
	AA	5,882,987	3/1999	Sirikrishnan	438	458		
	AB	5,906,951	5/1999	Chu et al.	438	751		
	AC	6,524,935	2/2003	Canaperi et al.	438	478		
	AD	6,573,126 B2	6/2003	Cheng et al.	438	149		
	AE	6,633,066 B1	10/2003	Bae et al.	257	347		
	AF	2003/0003679 A1	6/2003	Doyle et al.	438	406		
	AG	2003/0155568 A1	8/2003	Cheng et al.	257	12		
	A1	2003/0168654 A1	9/2003	Cheng et al.	257	19		
FOREIGN PATENT DOCUMENTS								
		DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION	
							YES	NO
	AJ	EP 1 248 294 A2	10/2002	Europe			X	
	AK	FR 2 818 010 (with English Abstract)	8/2002	France			X	
	AL	DE 101 00 194 A1	6/2001	Germany			X	
	AM	WO 02/15244 A2	2/2002	PCT			X	
	AN	WO 02/47156 A1	2/2002	PCT			X	
	AO	WO 99/53539	10/1999	PCT			X	
OTHER REFERENCES <i>(Including Author, Title, Date, Pertinent Pages, Etc.)</i>								
	AP	T. Tezuka et al., XP001109835, High-Performance Strained Si-on-Insulator MOSFETs by Novel Fabrication Processes Utilizing Ge-Condensation Technique , Symposium On VLSI Tech., Digest of Technical Papers. Honolulu, NY:IEEE US, pp. 96-97 (2002)						
	AQ	S. Mantl et al., "Strain relaxation of epitaxial SGe layers on Si(100) improved by hydrogen implantation" Nuclear Instruments and Methods in Physics Research , Vol. 147, No. 1-4, pp. 29-34 (1999)						
EXAMINER					DATE CONSIDERED			
*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609 ; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.								